

## GOA-340B

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|--|---|
| 1. Color                                       | Red                                       |
| 2. Material                                    | AlGaInP / GaP                             |
| 3. Electrode                                   | N(cathode) side : Au / P(anode) side : Au |
| 4. Electrode pattern                           | (Fig.)                                    |
| 5. Chip size                                   | 0.33 mm × 0.33 mm × 0.27 mmH (Fig.)       |
| 6. Chip structure                              | Face up: wire bonding                     |
| 7. Electro-Optical characteristics (Ta = 25°C) |   |

Parameters	Symbol	Condition	Characteristics			Unit
			Min.	Typ.	Max.	
Brightness*	Iv	IF = 20mA	250	400	—	mcd
Forward Voltage	VF	IF = 20mA	1.8	2.2	2.4	V
Reverse Current	IR	VR = 5V	—	—	10	μA
Dominant Wavelength	λd	IF = 20mA	615	620	625	nm

\*Brightness Measurement at Resonac Photonics.

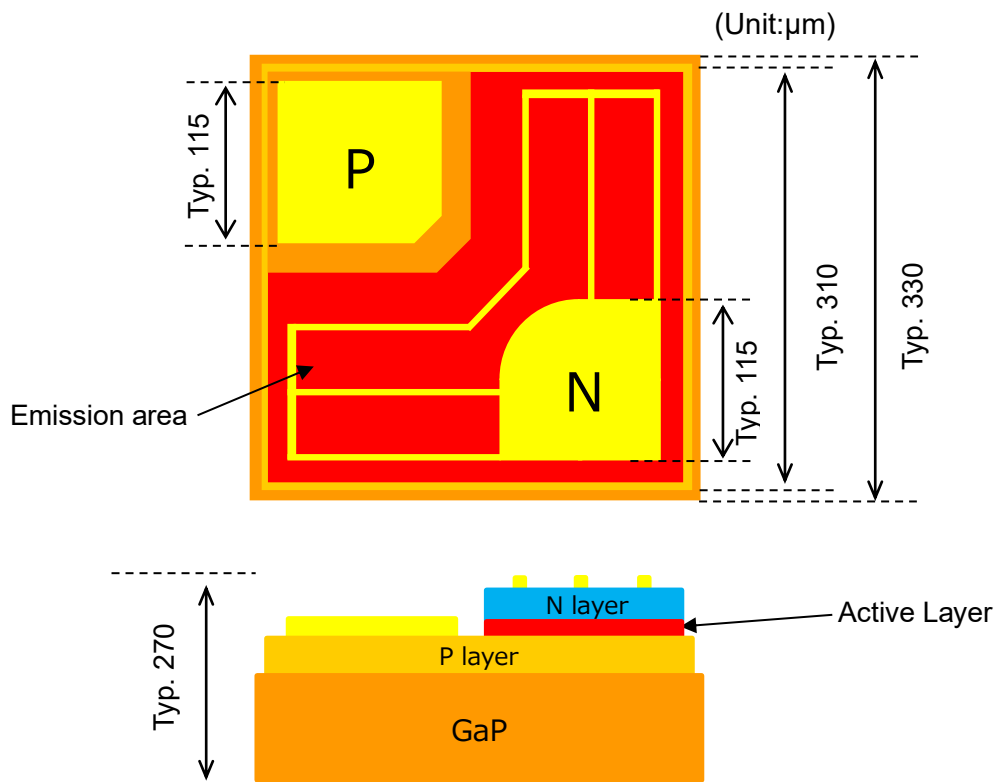


Fig. Chip size & Emission area

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